

MGFC42V7785A

7.7 ~ 8.5GHz BAND 16W INTERNALLY MATCHED GaAs FET

DESCRIPTION

The MGFC42V7785A is an internally impedance-matched GaAs power FET especially designed for use in 7.7 ~ 8.5 GHz band amplifiers. The hermetically sealed metal-ceramic package guarantees high reliability.

FEATURES

- Class A operation
- Internally matched to 50(ohm) system
- High output power
P1dB = 16W (TYP.) @ f=7.7~8.5GHz
- High power gain
GLP = 7 dB (TYP.) @ f=7.7~8.5GHz
- High power added efficiency
P.A.E. = 28 % (TYP.) @ f=7.7~8.5GHz
- Low distortion [item -51]
IM3= -45 dBc(TYP.) @Po=32dBm S.C.L.

APPLICATION

- item 01 : 7.7~8.5 GHz band power amplifier
- item 51 : 7.7~8.5 GHz band digital radio communication

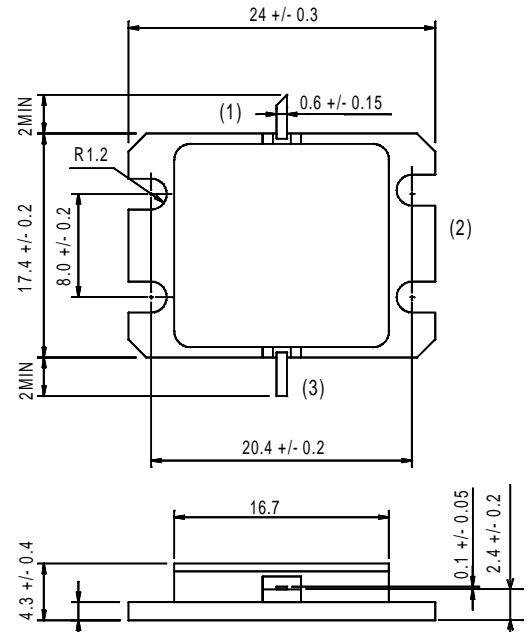
QUALITY GRADE

IG

RECOMMENDED BIAS CONDITIONS

- VDS = 10 (V)
- ID = 4.5 (A) Refer to Bias Procedure
- RG= 25 (ohm)

OUTLINE DRAWING Unit:millimeters (inches)



- (1) GATE
- (2) SOURCE(FIANGE)
- (3) DRAIN

ABSOLUTE MAXIMUM RATINGS (Ta=25 deg.C)

Symbol	Parameter	Ratings	Unit
VGDO	Gate to drain voltage	-15	V
VGSO	Gate to source voltage	-15	V
ID	Drain current	15	A
IGR	Reverse gate current	-40	mA
IGF	Forward gate current	84	mA
PT	Total power dissipation *1	93.7	W
Tch	Channel temperature	175	deg.C
Tstg	Storage temperature	-65 / +175	deg.C

*1 : Tc=25 deg.C

< Keep safety first in your circuit designs! >

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ELECTRICAL CHARACTERISTICS (Ta=25 deg.C)

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
IDSS	Saturated drain current	VDS=3V, VGS=0V	-	9	12	A
gm	Transconductance	VDS=3V, ID=4.4A	-	4	-	S
VGS(off)	Gate to source cut-off voltage	VDS=3V, ID=80mA	-2	-	-4	V
P1dB	Output power at 1dB gain compression	VDS=10V, ID(RF off)=4.5A, f=7.7~8.5GHz	41	42	-	dBm
GLP	Linear power gain		6	7	-	dB
ID	Drain current		-	4	-	A
P.A.E.	Power added efficiency		-	28	-	%
IM3	3rd order IM distortion *1		-42	-45	-	dBc
Rth(ch-c)	Thermal resistance *2		Delta Vf method	-	-	1.6

*1 : item -51, 2 tone test, Po=32dBm Single Carrier Level, f=8.5GHz, Delta f=10MHz

*2 : Channel to case

MGFC42V7785A**7.7 ~ 8.5GHz BAND 16W INTERNALLY MATCHED GaAs FET****Requests Regarding Safety Designs**

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